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Supporting Information

Preparation of band gap grading Cu₂ZnSn(S,Se)₄ thin film solar cells by the Post-Sulfo-Selenization treatment

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In Supplementary Information, we have provided sample data without bandgap gradient after PSS treatment. It is used to illustrate the degree which the band gap grading effect can improve the performance of thin film solar cell. The sample is named PSS-ng.







Fig.S2 The J-V characteristic of the sample PSS-ng.

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Sample	V _{oc} (mV)	J _{sc} (mA/cm ²)	FF (%)	PCE (%)	Rs ($\Omega \cdot cm^2$)	$\operatorname{Rsh}\left(\Omega\cdot \mathrm{cm}^{2}\right)$
PSS-ng	507.75	32.68	49.59	8.23	3.85	103.5



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-2.0 -1.8 -1.6 -1.4

Fig.S3 The C-V and $N_{c\mbox{-v}}$ curves of the sample PSS-ng. These data were taken under a 0 to -2 V reverse bias at 300 K.

-0.8 -0.6 -0.4 -0.2 0.0

-1.2 -1.0

Voltage (V)

 10^{17}

0.2

0.3

V_{bias}= 0 V W_d= 0.319 μm

0.4

0.5

Profiling Position (µm)

0.6

0.7

0.8

Table.S1 The parameters of the PSS-ng device.